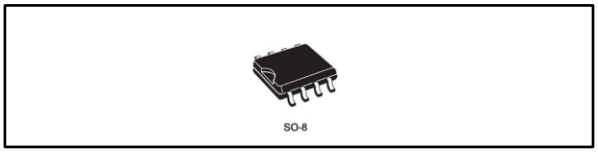
VN7140AS12

High-side driver with Multisense analog feedback for automotive applications

Datasheet - production data



Features

Max transient supply voltage	V_{CC}	40 V
Operating voltage range	V_{CC}	4 to 28 V
Typ. on-state resistance (per Ch)	R_{ON}	140 mΩ
Minimum cranking supply voltage (V_{CC} decreasing)	$V_{USD\_Cranking}$	2.85 V
Current limitation (typ.)	I_{LIMH}	12 A
Standby current (max.)	I_{STBY}	0.5 µA

- AEC-Q100 qualified
- Extreme low voltage operation for deep cold cranking applications (compliant with LV124, revision 2013)
- General
  - Single channel smart high-side driver with Multisense analog feedback
  - Very low standby current
  - Compatible with 3 V and 5 V CMOS outputs
- Multisense diagnostic functions
  - Analog feedback of load current with high precision proportional current mirror
  - Overload and short to ground (power limitation) indication
  - Thermal shutdown indication
  - OFF-state open-load detection
  - Output short to V_{CC} detection
  - Sense enable/disable
- Protections
  - Undervoltage shutdown
  - Overvoltage clamp
  - Load current limitation
  - Self limiting of fast thermal transients
  - Loss of ground and V_{CC}
  - Reverse battery with external components
  - Electrostatic discharge protection

Applications

- All types of automotive resistive, inductive and capacitive loads
- Specially intended for automotive signal lamps (up to R10W or LED Rear Combinations)

Description

The device is single channel high-side driver manufactured using ST proprietary VIPower® M0-7 technology and housed in the SO-8 package. It is designed to drive 12 V automotive grounded loads through a 3 V and 5 V CMOS-compatible interface, and to provide protection and diagnostics.

The device integrates advanced protective functions such as load current limitation, overload active management by power limitation and overtemperature shutdown.

A dedicated Multisense pin delivers high precision proportional load current sense, in addition to the detection of overload and short circuit to ground, short to V_{CC} and OFF-state open-load.

A sense enable pin allows OFF-state diagnosis to be disabled during the module low-power mode as well as external sense resistor sharing among similar devices.

This is information on a product in full production.

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1 Block diagram and pin description

Figure 1: Block diagram

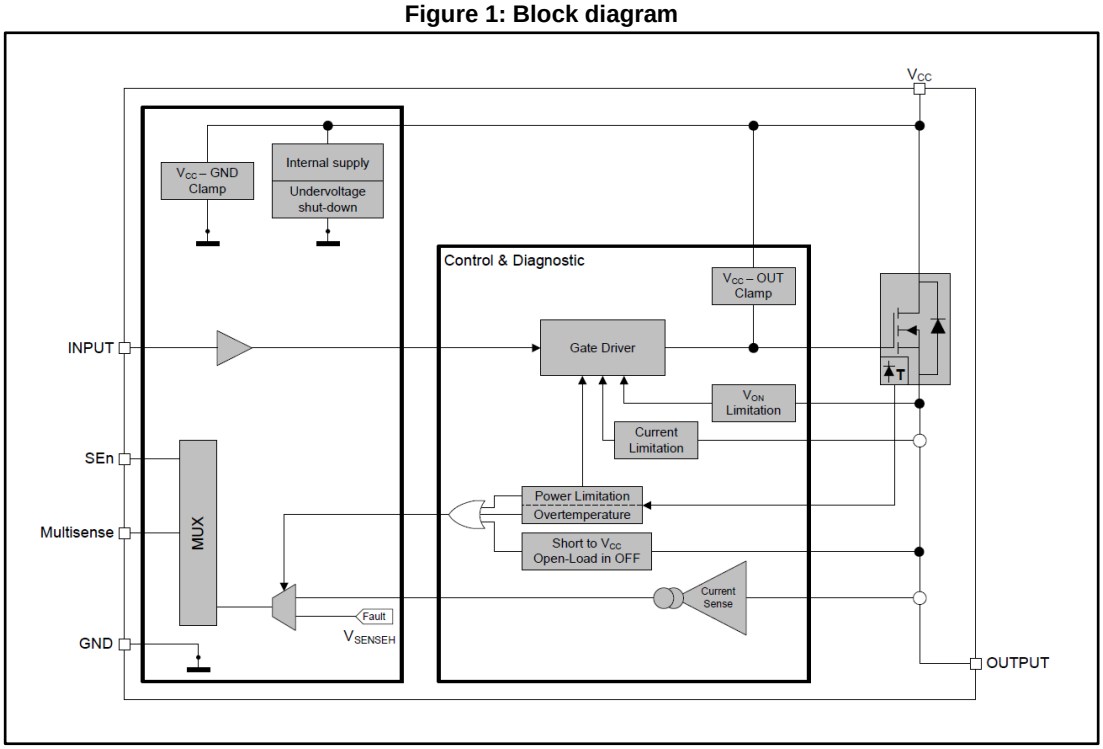


Table 1: Pin functions

Name	Function
V_{CC}	Battery connection.
OUTPUT	Power outputs.
GND	Ground connection. Must be reverse battery protected by an external diode / resistor network.
INPUT	Voltage controlled input pin with hysteresis, compatible with 3 V and 5 V CMOS outputs. It controls output switch state.
Multisense	Multiplexed analog sense output pin; it delivers a current proportional to the load current.
SEn	Active high compatible with 3 V and 5 V CMOS outputs pin; it enables the Multisense diagnostic pin.

Figure 2: Configuration diagram (top view)

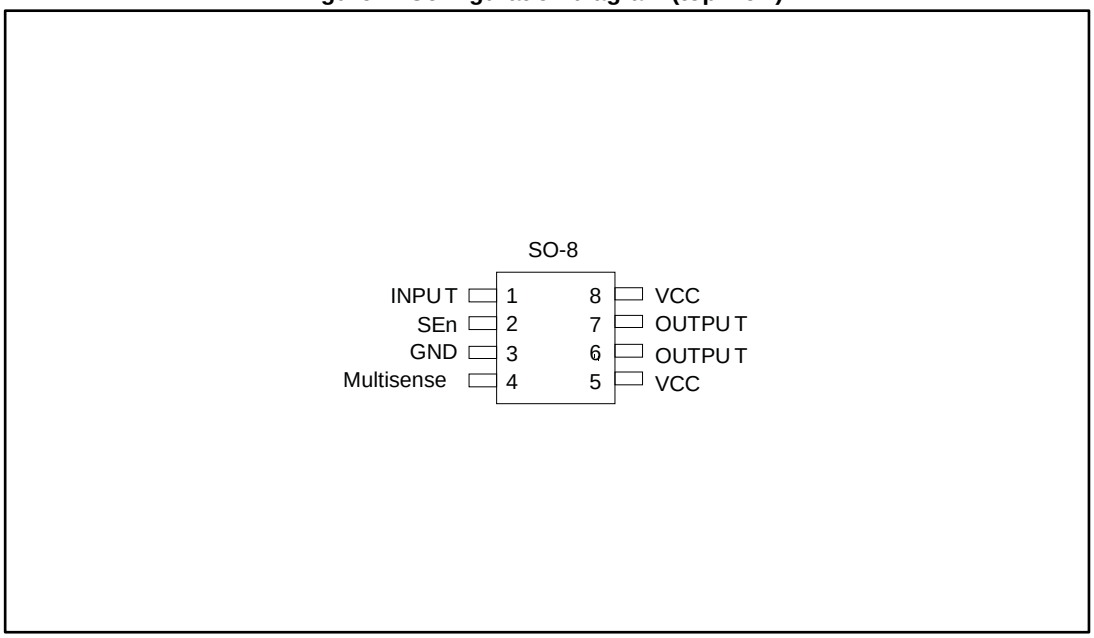


Table 2: Suggested connections for unused and not connected pins

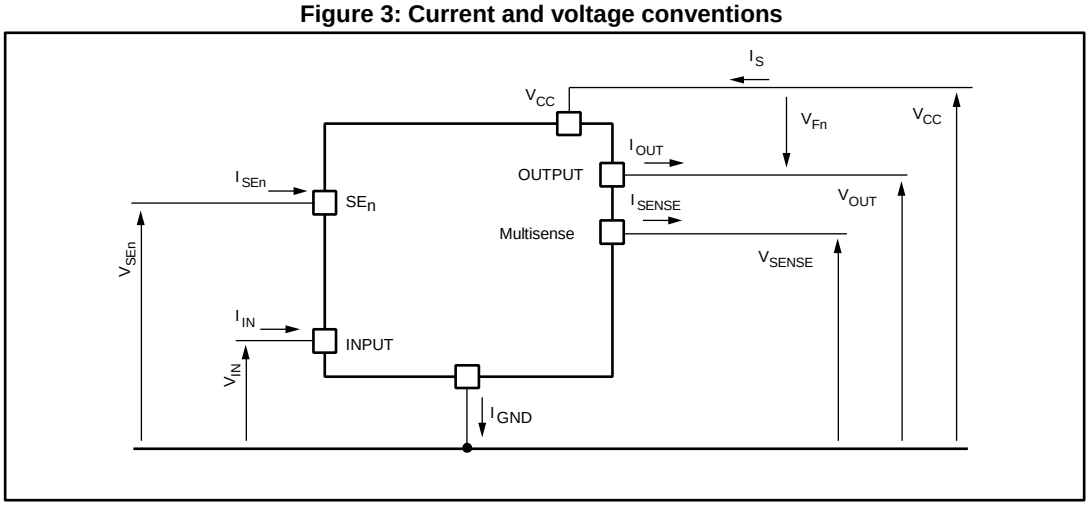
Connection/pin	Multisense	N.C.	Output	Input	SEn
Floating	Not allowed	X (1)	X	X	X
To ground	Through 1 kΩ resistor	X	Not allowed	Through 15 kΩ resistor	Through 15 kΩ resistor

Notes:

(1)X: do not care.

2 Electrical specification

Figure 3: Current and voltage conventions



$V_F = V_{OUT} - V_{CC}$ during reverse battery condition.

2.1 Absolute maximum ratings

The following table shows the device stress ratings; the device operation at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to the conditions in the table below for extended periods may affect device reliability.

Table 3: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	38	V
$-V_{CC}$	Reverse DC supply voltage	0.3	
V_{CCPK}	Maximum transient supply voltage (ISO 16750-2:2010 Test B clamped to 40 V; R_L = 4 Ω)	40	V
V_{CCJS}	Maximum jump start voltage for single pulse short circuit protection	28	V
$-I_{GND}$	DC reverse ground pin current	200	mA
I_{OUT}	OUTPUT DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	3	
I_{IN}	INPUT DC input current	-1 to 10	mA
I_{SEn}	SEn DC input current		
I_{SENSE}	Multisense pin DC output current (V_{GND} = V_{CC} and V_{SENSE} < 0 V)	10	mA
	Multisense pin DC output current in reverse (V_{CC} < 0 V)	-20	

Symbol	Parameter	Value	Unit
E_{MAX}	Maximum switching energy (single pulse) (T_{DEMAG} = 0.4 ms; T_{jstart} = 150 °C)	10	mJ
V_{ESD}	Electrostatic discharge (JEDEC 22A-114F) • INPUT • Multisense • SEn • OUTPUT • V_{CC}	 4000 2000 4000 4000 4000	 V V V V V
V_{ESD}	Charge device model (CDM-AEC-Q100-011)	750	V
T_j	Junction operating temperature	-40 to 150	°C
T_{stg}	Storage temperature	-55 to 150	

2.2 Thermal data

Table 4: Thermal data

Symbol	Parameter	Typ. value	Unit
$R_{thj\text{-}board}$	Thermal resistance junction-board (JEDEC JESD 51-8) (1)(1)	31	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient (JEDEC JESD 51-2)(2)	71	
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient (JEDEC JESD 51-2)(1)	48.5	

Notes:

(1)Device mounted on four-layers 2s2p PCB

(2)Device mounted on two-layers 2s0p PCB with 2 cm^2 heatsink copper trace

2.3 Main electrical characteristics

7 V < V_{CC} < 28 V; -40°C < T_j < 150°C, unless otherwise specified.

All typical values refer to V_{CC} = 13 V; T_j = 25°C, unless otherwise specified.

Table 5: Electrical characteristics during cranking

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{USD\_Cranking}$	Minimum cranking supply voltage (V_{CC} decreasing)				2.85	V
R_{ON}	On-state resistance	I_{OUT} = 0.2 A; V_{CC} = 2.85 V; V_{CC} decreasing			1400	mΩ
T_{TSD}(1)	Shutdown temperature (V_{CC} decreasing)	V_{CC} = 2.85 V	140			°C

Notes:

(1)Parameter guaranteed by design and characterization; not subject to production test.

Table 6: Power section

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC}	Operating supply voltage		4	13	28	V
V_{USD}	Undervoltage shutdown				2.85	V
$V_{USDReset}$	Undervoltage shutdown reset				5	V
$V_{USDhyst}$	Undervoltage shutdown hysteresis			0.3		V
R_{ON}	On-state resistance	I_{OUT} = 1 A; T_j = 25 °C		140		mΩ
		I_{OUT} = 1 A; T_j = 150 °C			280	
		I_{OUT} = 1 A; V_{CC} = 4 V; T_j = 25 °C			210	
V_{clamp}	Clamp voltage	I_S = 20 mA; 25°C < T_j < 150 °C	41	46	52	V
		I_S = 20 mA; T_j = -40 °C	38			V
I_{STBY}	Supply current in standby at V_{CC} = 13 V (1)	V_{CC} = 13 V; V_{IN} = V_{OUT} = V_{SEn} = 0 V; T_j = 25 °C			0.5	µA
		V_{CC} = 13 V; V_{IN} = V_{OUT} = V_{SEn} = 0 V; T_j = 85 °C (2)			0.5	
		V_{CC} = 13 V; V_{IN} = V_{OUT} = V_{SEn} = 0 V; T_j = 125°C			3	
t_{D_STBY}	Standby mode blanking time	V_{CC} = 13 V; V_{IN} = V_{OUT} = 0 V; V_{SEn} = 5 V to 0 V	60	300	550	µs
$I_{S(ON)}$	Supply current	V_{CC} = 13 V; V_{SEn} = 0 V; V_{IN} = 5 V; I_{OUT} = 0 A		3	5	mA
$I_{GND(ON)}$	Control stage current consumption in ON-state. All channels active.	V_{CC} = 13 V; V_{SEn} = 5 V; V_{IN} = 5 V; I_{OUT} = 1 A			6	mA
$I_{L(off)}$	Off-state output current at V_{CC} = 13 V	V_{IN} = V_{OUT} = 0 V; V_{CC} = 13 V; T_j = 25 °C	0	0.01	0.5	µA
		V_{IN} = V_{OUT} = 0 V; V_{CC} = 13 V; T_j = 125 °C	0		3	
V_F	Output - V_{CC} diode voltage	I_{OUT} = -1 A; T_j = 150 °C			0.7	V

Notes:

(1)PowerMOS leakage included.

(2)Parameter specified by design; not subject to production test.

Table 7: Switching

V_{CC} = 13 V; -40 °C < T_j < 150 °C, unless otherwise specified						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
$t_{d(on)}$(1)(1)	Turn-on delay time at T_j = 25 °C	R_L = 13 Ω	10	70	120	µs
$t_{d(off)}$(1)	Turn-off delay time at T_j = 25 °C		10	40	100	
$(dV_{OUT}/dt)_{on}$(1)	Turn-on voltage slope at T_j = 25 °C	R_L = 13 Ω	0.1	0.27	0.7	V/µs
$(dV_{OUT}/dt)_{off}$(1)	Turn-off voltage slope at T_j = 25 °C		0.1	0.35	0.7	
W_{ON}	Switching energy losses at turn-on (t_{won})	R_L = 13 Ω	—	0.15	0.18(2)(2)	mJ
W_{OFF}	Switching energy losses at turn-off (t_{woff})	R_L = 13 Ω	—	0.1	0.18(2)	mJ
t_{SKEW}(1)	Differential Pulse skew (t_{PHL} - t_{PLH})	R_L = 13 Ω	-100	-50	0	µs

Notes:

(1)See*Figure 6: "Switching time and pulse skew"*

(2)Parameter guaranteed by design and characterization; not subject to production test.

Table 8: Logic inputs

7 V < V_{CC} < 28 V; -40 °C < T_j < 150 °C						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Input characteristics						
V_{IL}	Input low level voltage				0.9	V
I_{IL}	Low level input current	V_{IN} = 0.9 V	1			µA
V_{IH}	Input high level voltage		2.1			V
I_{IH}	High level input current	V_{IN} = 2.1 V			10	µA
$V_{I(hyst)}$	Input hysteresis voltage		0.2			V
V_{ICL}	Input clamp voltage	I_{IN} = 1 mA	5.3		7.2	V
		I_{IN} = -1 mA		-0.7		
SEn characteristics (7 V < V_{CC} < 18 V)						
V_{SEnL}	Input low level voltage				0.9	V
I_{SEnL}	Low level input current	V_{IN} = 0.9 V	1			µA
V_{SEnH}	Input high level voltage		2.1			V
I_{SEnH}	High level input current	V_{IN} = 2.1 V			10	µA
$V_{SEn(hyst)}$	Input hysteresis voltage		0.2			V
V_{SEnCL}	Input clamp voltage	I_{IN} = 1 mA	5.3		7.2	V
		I_{IN} = -1 mA		-0.7		

Table 9: Protections

7 V < V_{CC} < 18 V; -40 °C < T_j < 150 °C						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
I_{LIMH}	DC short circuit current	V_{CC} = 13 V	8	12	16	A
		4 V < V_{CC} < 18 V (1)(1)				
I_{LIML}	Short circuit current during thermal cycling	V_{CC} = 13 V; T_R < T_j < T_{TSD}		4		
T_{TSD}	Shutdown temperature		150	175	200	°C
T_R	Reset temperature(1)		T_{RS} + 1	T_{RS} + 7		
T_{RS}	Thermal reset of fault diagnostic indication	V_{SEn} = 5 V	135			
T_{HYST}	Thermal hysteresis(T_{TSD} - T_R)(1)			7		
ΔT_{J_SD}	Dynamic temperature	T_j = -40°C; V_{CC} = 13 V		60		K
V_{DEMAG}	Turn-off output voltage clamp	I_{OUT} = 1 A; L = 6 mH; T_j = -40°C	V_{CC} - 38			V
		I_{OUT} = 1 A; L = 6 mH; T_j = 25°C to 150°C	V_{CC} - 41	V_{CC} - 46	V_{CC} - 52	V
V_{ON}	Output voltage drop limitation	I_{OUT} = 0.07 A		20		mV

Notes:

(1)Parameter guaranteed by design and characterization; not subject to production test.

Table 10: Multisense

7 V < V_{CC} < 18 V; -40 °C < T_j < 150 °C						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
V_{SENSE_CL}	Multisense clamp voltage	V_{SEn} = 0 V; I_{SENSE} = 1 mA	-17		-12	V
		V_{SEn} = 0 V; I_{SENSE} = -1 mA		7		
Current sense characteristics						
K_{OL}	I_{OUT}/I_{SENSE}	I_{OUT} = 0.01 A; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	295			
dK_{cal}/K_{cal}(1)(1)(2)(2)	Current sense ratio drift at calibration point	I_{OUT} = 0.01 A to 0.025 A; I_{cal} = 17.5 mA; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	-30		30	%
K_{LED}	I_{OUT}/I_{SENSE}	I_{OUT} = 0.025 A; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	330	580	820	
dK_{LED}/K_{LED}(1)(2)	Current sense ratio drift	I_{OUT} = 0.025 A; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	-25		25	%
K_0	I_{OUT}/I_{SENSE}	I_{OUT} = 0.07 A; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	375	550	720	
dK_0/K_0(1)(2)	Current sense ratio drift	I_{OUT} = 0.07 A; V_{SENSE} = 0.5 V; V_{SEn} = 5 V	-20		20	%

7 V < V_{CC} < 18 V; -40 °C < T_j < 150 °C						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
K_1	I_{OUT}/I_{SENSE}	I_{OUT} = 0.15 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	360	500	670	
dK_1/K_1 (1)(2)	Current sense ratio drift	I_{OUT} = 0.15 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	-15		15	%
K_2	I_{OUT}/I_{SENSE}	I_{OUT} = 0.7 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	380	475	570	
dK_2/K_2 (1)(2)	Current sense ratio drift	I_{OUT} = 0.7 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	-10		10	%
K_3	I_{OUT}/I_{SENSE}	I_{OUT} = 2 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	430	470	520	
dK_3/K_3 (1)(2)	Current sense ratio drift	I_{OUT} = 2 A; V_{SENSE} = 4 V; V_{SEn} = 5 V	-5		5	%
I_{SENSE0}	Multisense leakage current	Multisense disabled: V_{SEn} = 0 V	0		0.5	µA
		Multisense disabled: -1 V < V_{SENSE} < 5 V (1)	-0.5		0.5	
		Multisense enabled: V_{SEn} = 5 V; Channel ON; I_{OUT} = 0 A; Diagnostic selected; V_{IN} = 5 V; I_{OUT} = 0 A	0		2	
		Multisense enabled: V_{SEn} = 5 V; Channel OFF; Diagnostic selected: V_{IN} = 0 V;	0		2	
V_{OUT_MSD} (1)	Output voltage for Multisense shutdown	V_{IN} = 5 V; V_{SEn} = 5 V; R_{SENSE} = 2.7 kΩ; I_{OUT} = 1 A		5		V
V_{SENSE_SAT}	Multisense saturation voltage	V_{CC} = 7 V; R_{SENSE} = 2.7 kΩ; V_{SEn} = 5 V; V_{IN} = 5 V; I_{OUT} = 2 A; T_j = 150°C	5			V
I_{SENSE_SAT} (1)	Multisense saturation current	V_{CC} = 7 V; V_{SENSE} = 4 V; V_{IN} = 5 V; V_{SEn} = 5 V; T_j = 150 °C	4			mA
I_{OUT_SAT} (1)	Output saturation current	V_{CC} = 7 V; V_{SENSE} = 4 V; V_{IN} = 5 V; V_{SEn} = 5 V; T_j = 150°C	2.2			A
OFF-state diagnostic						
V_{OL}	OFF-state open-load voltage detection threshold	V_{IN} = 0 V; V_{SEn} = 5 V;	2	3	4	V
$I_{L(off2)}$	OFF-state output sink current	V_{IN} = 0 V; V_{OUT} = V_{OL}; T_j = -40 °C to 150 °C	-100		-15	µA
t_{DSTKON}	OFF-state diagnostic delay time from falling edge of INPUT (see)*Figure 8: "TDSTKON"*	V_{IN} = 5 V to 0 V; V_{SEn} = 5 V; I_{OUT} = 0 A; V_{OUT} = 4 V	100	350	700	µs

7 V < V_{CC} < 18 V; -40 °C < T_j < 150 °C						
Symbol	**Parameter**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
$t_{D\_OL\_V}$	Settling time for valid OFF-state open load diagnostic indication from rising edge of SEn	V_{IN} = 0 V; V_{OUT} = 4 V; V_{SEn} = 0 V to 5 V			60	µs
t_{D_VOL}	OFF-state diagnostic delay time from rising edge of V_{OUT}	V_{IN} = 0 V; V_{SEn} = 5 V; V_{OUT} = 0 V to 4 V		5	30	µs
Fault diagnostic feedback (see)*Table 11: "Truth table"*						
V_{SENSEH}	Multisense output voltage in fault condition	V_{CC} = 13 V; V_{IN} = 0 V; V_{SEn} = 5 V; I_{OUT} = 0 A; V_{OUT} = 4 V; R_{SENSE} = 1 kΩ;	5		6.6	V
I_{SENSEH}	Multisense output current in fault condition	V_{CC} = 13 V; V_{SENSE} = 5 V	7	20	30	mA
Multisense timings (current sense mode - see)(3)*Figure 7: "Multisense timings (current sense mode)"*						
$t_{DSENSE1H}$	Current sense settling time from rising edge of SEn	V_{IN} = 5 V; V_{SEn} = 0 V to 5 V; R_{SENSE} = 1 kΩ; R_L = 13 Ω			60	µs
$t_{DSENSE1L}$	Current sense disable delay time from falling edge of SEn	V_{IN} = 5 V; V_{SEn} = 5 V to 0 V; R_{SENSE} = 1 kΩ; R_L = 13 Ω		5	20	µs
$t_{DSENSE2H}$	Current sense settling time from rising edge of INPUT	V_{IN} = 0 V to 5 V; V_{SEn} = 5 V; R_{SENSE} = 1 kΩ; R_L = 13 Ω		100	250	µs
$\Delta t_{DSENSE2H}$	Current sense settling time from rising edge of I_{OUT} (dynamic response to a step change of I_{OUT})	V_{IN} = 5 V; V_{SEn} = 5 V; R_{SENSE} = 1 kΩ; I_{SENSE} = 90 % of $I_{SENSEMAX}$; R_L = 13 Ω			100	µs
$t_{DSENSE2L}$	Current sense turn-off delay time from falling edge of input	V_{IN} = 5 V to 0 V; V_{SEn} = 5 V; R_{SENSE} = 1 kΩ; R_L = 13 Ω		50	250	µs

Notes:

(1)Parameter specified by design; not subject to production test.

(2)All values refer to V_{CC} = 13 V; T_j = 25°C, unless otherwise specified.

(3)Transition delays are measured up to +/- 10% of final conditions.

Figure 4: IOUT/ISENSE versus IOUT

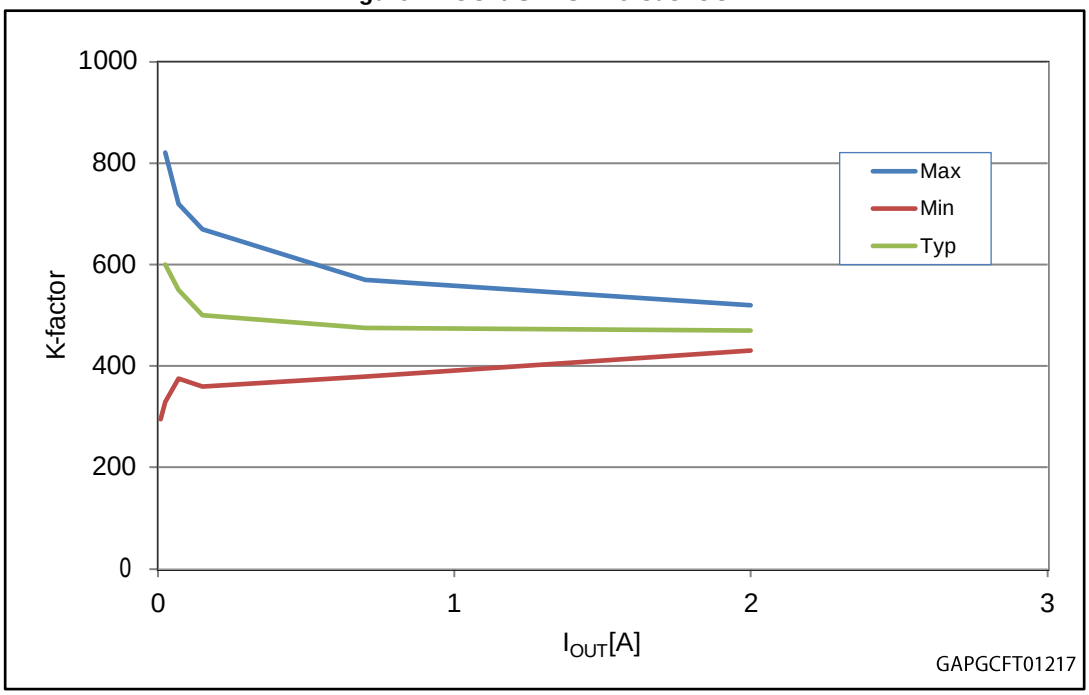


Figure 5: Current sense accuracy versus IOUT

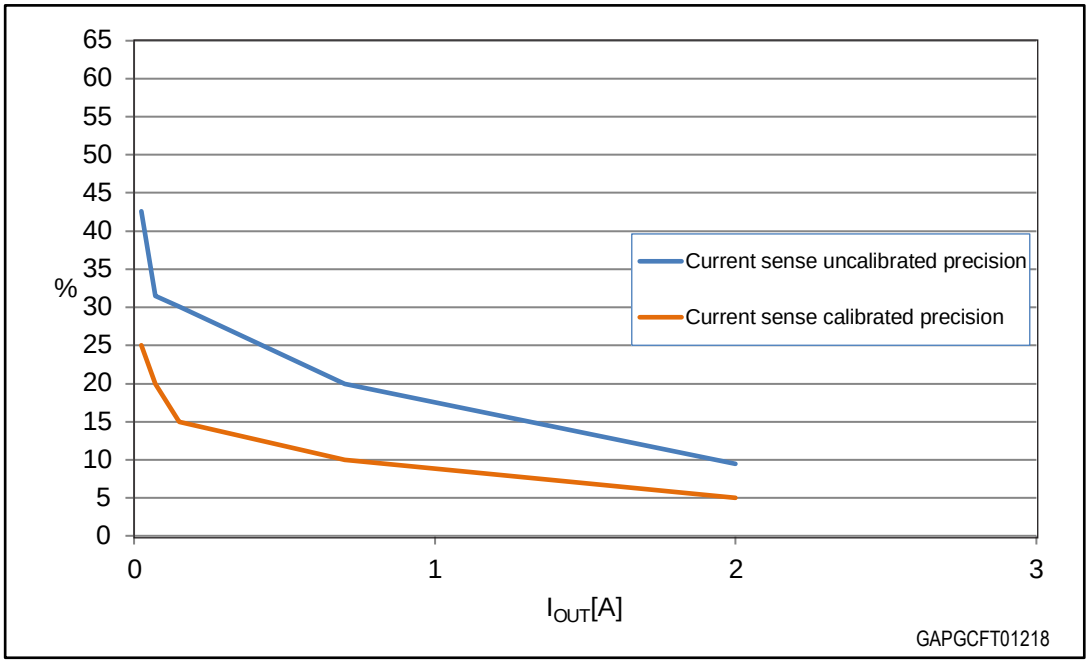


Figure 6: Switching time and pulse skew

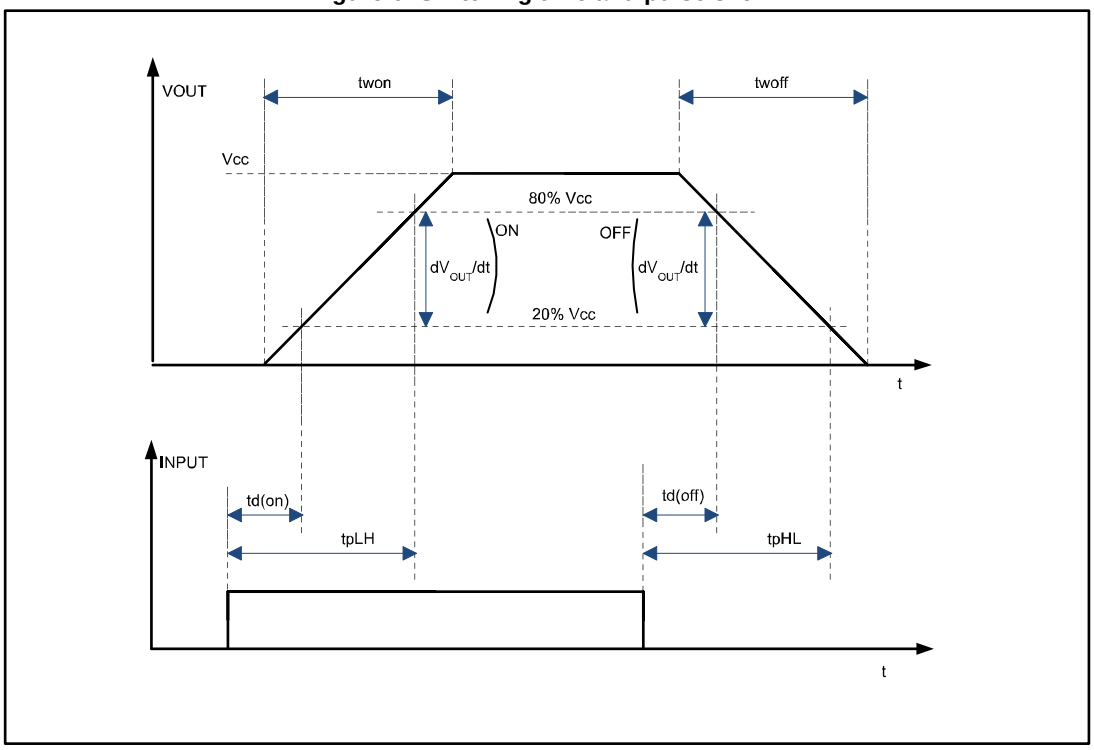


Figure 7: Multisense timings (current sense mode)

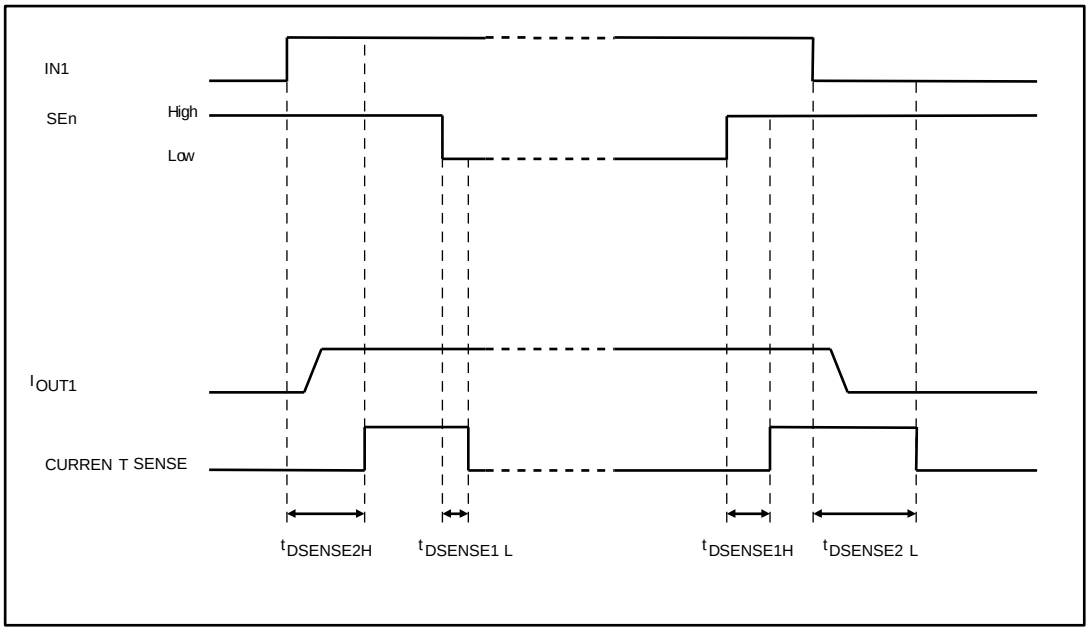


Figure 8: TDSTKON

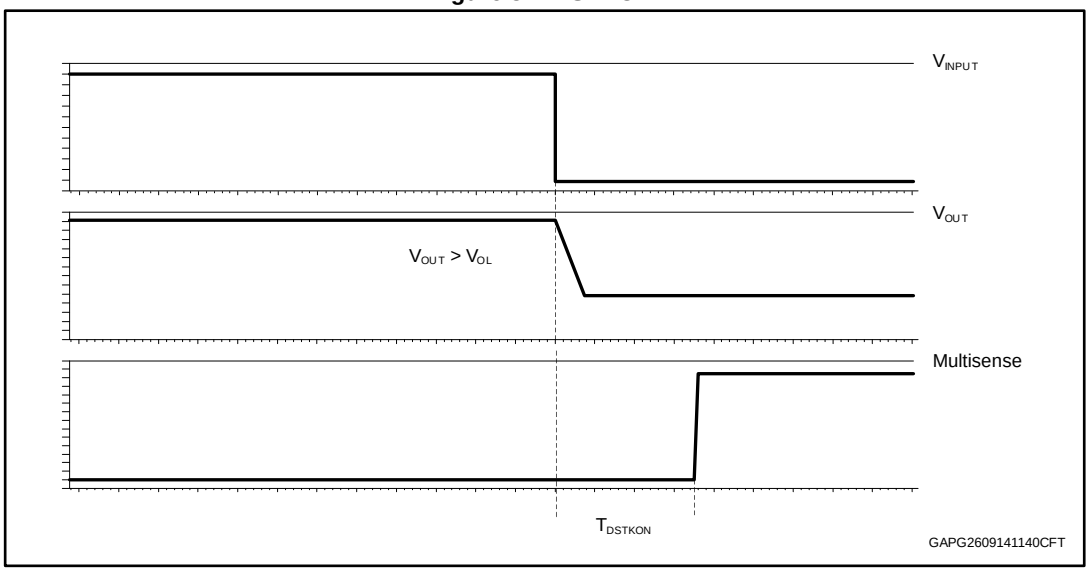


Table 11: Truth table

Mode	Conditions	IN_X	SEn	OUT_X	Multisense	Comments
Standby	All logic inputs low	L	L	L	Hi-Z	Low quiescent current consumption
Normal	Nominal load connected; T_j < 150 °C	L		L	Hi-Z	
		H		H	I_{SENSE} = 1/K * I_{OUT}	Outputs configured for auto-restart
Overload	Overload or short to GND causing: $T_j > T_{TSD}$ or $\Delta T_j > \Delta T_{j\_SD}$	L		L	Hi-Z	
		H		H	V_{SENSE} = V_{SENSEH}	Output cycles with temperature hysteresis
Undervoltage	$V_{CC} < V_{USD}$ (falling)	X	X	L	Hi-Z	Re-start when $V_{CC} > V_{USD}$ + $V_{USDhyst}$ (rising)
OFF-state diagnostics	Short to V_{CC}	L		H	V_{SENSE} = V_{SENSEH}	
	Open-load	L		H	V_{SENSE} = V_{SENSEH}	External pull-up
Negative output voltage	Inductive loads turn-off	L		< 0 V	Hi-Z	

2.4 Waveforms

Figure 9: Standby mode activation

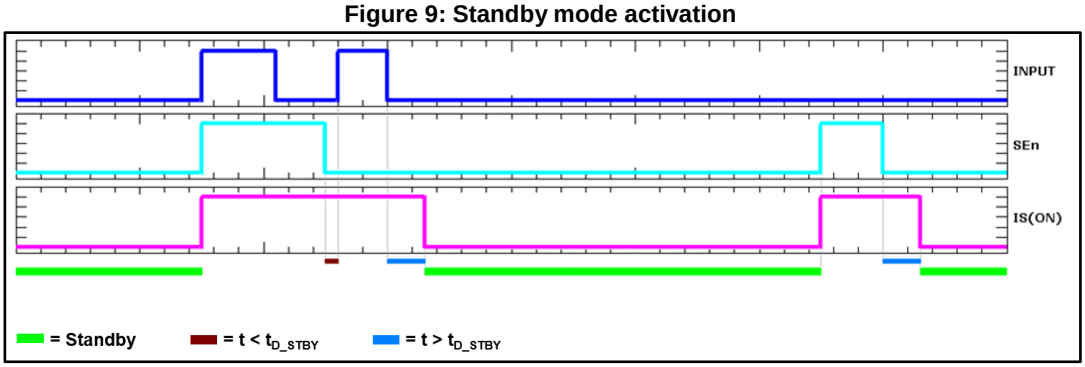
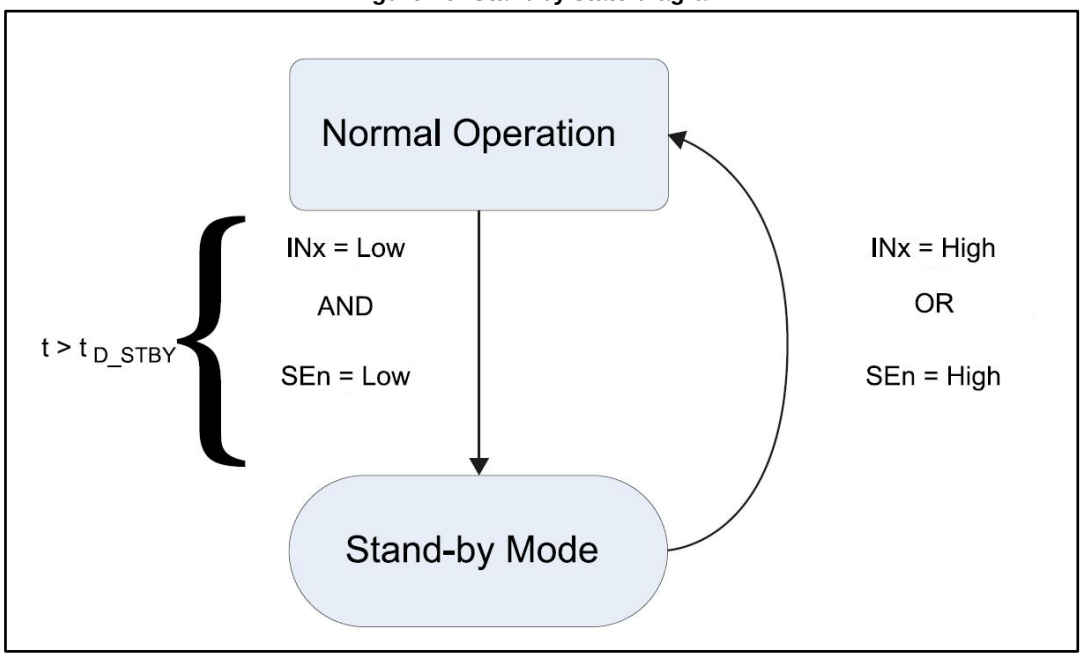


Figure 10: Standby state diagram



2.5 Electrical characteristics curves

Figure 11: OFF-state output current

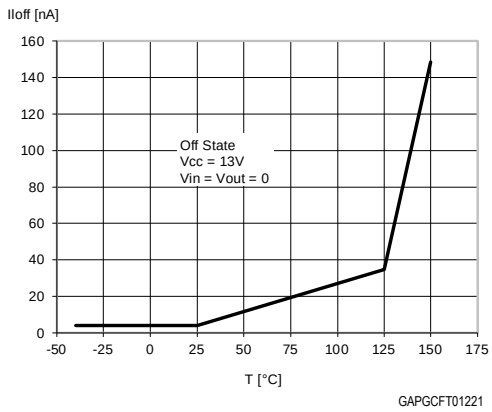


Figure 12: Standby current

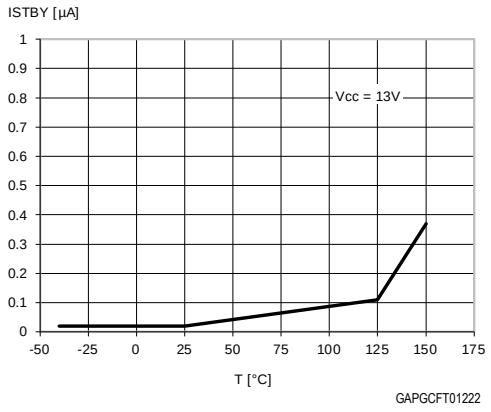


Figure 13: IGND(ON) vs. Tcase

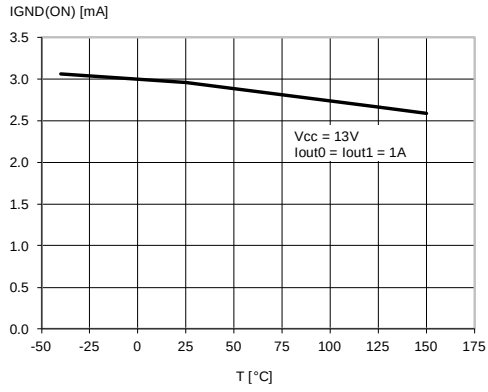


Figure 14: Logic input high level voltage

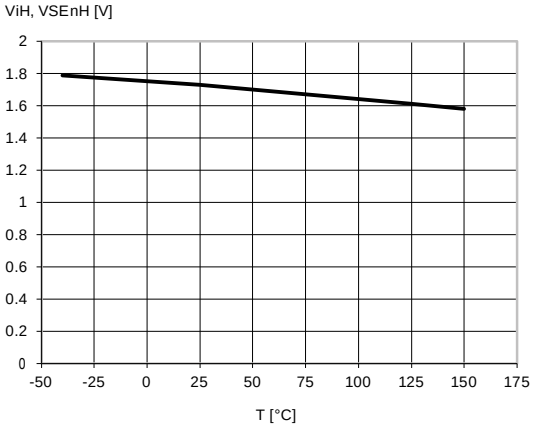


Figure 15: Logic input low level voltage

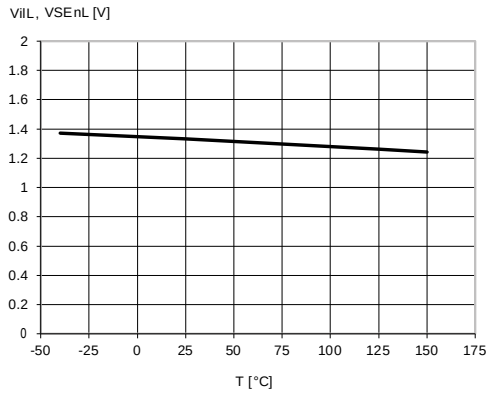


Figure 16: High level logic input current

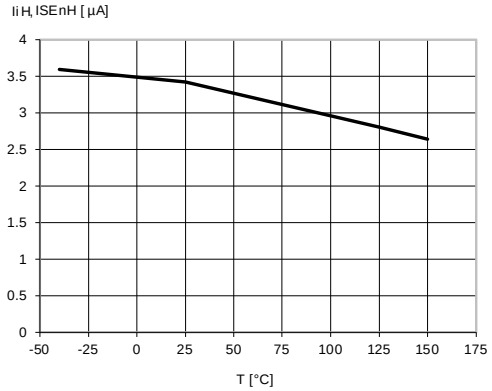


Figure 17: Low level logic input current

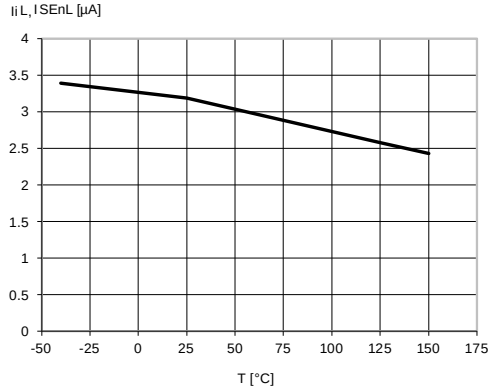


Figure 18: Logic input hysteresis voltage

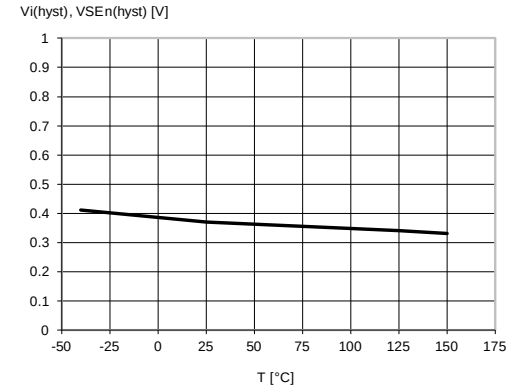


Figure 19: On-state resistance vs. Tcase

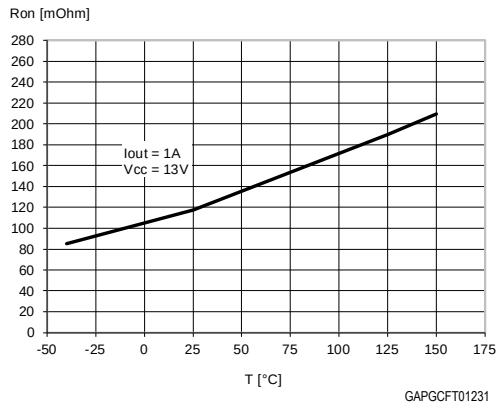


Figure 20: On-state resistance vs. VCC

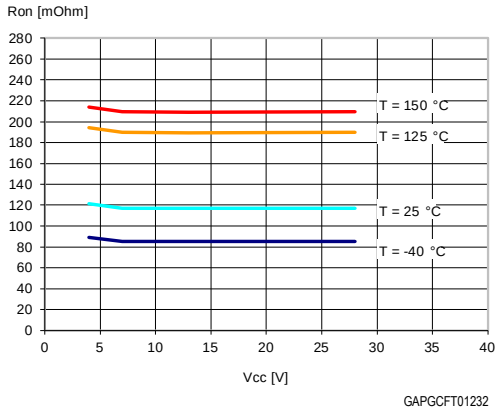


Figure 21: Turn-on voltage slope

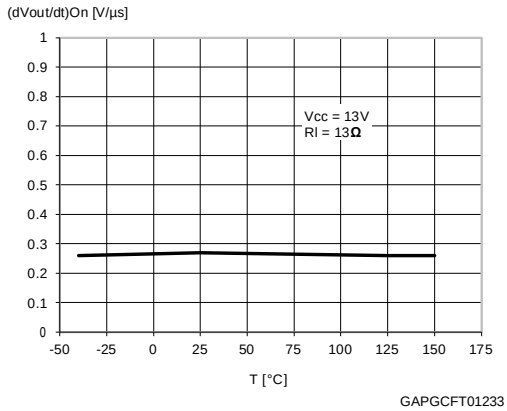


Figure 22: Turn-off voltage slope

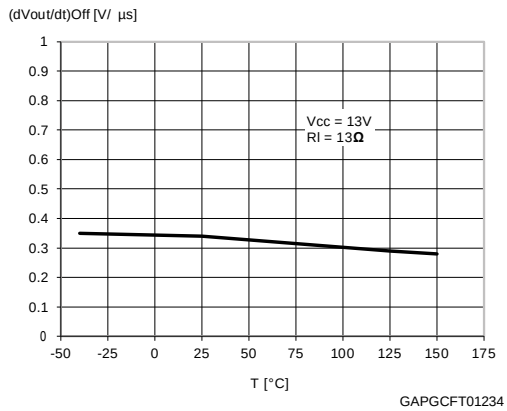


Figure 23: Won vs. Tcase

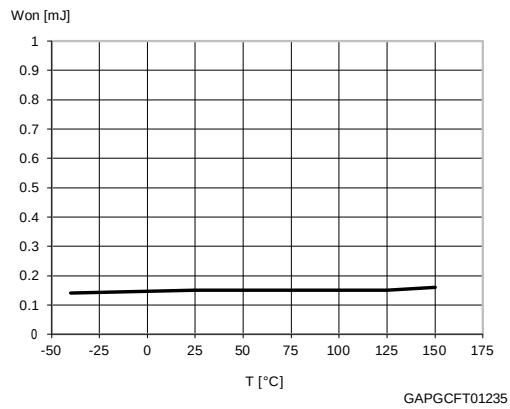


Figure 24: Woff vs. Tcase

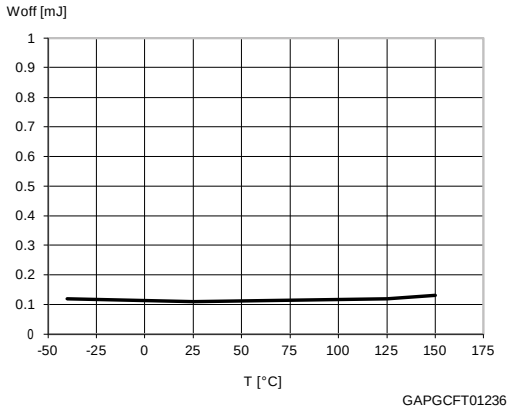


Figure 25: ILIMH vs. Tcase

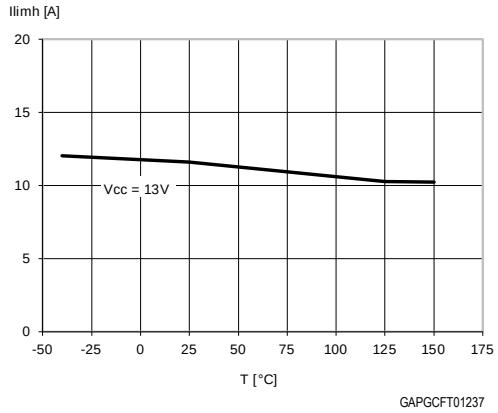


Figure 26: OFF-state open-load voltage detection threshold

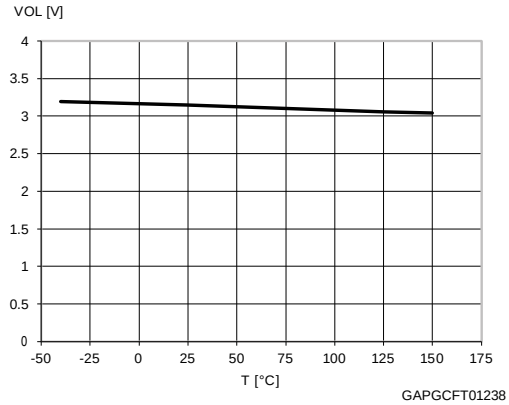


Figure 27: Vsense clamp vs. Tcase

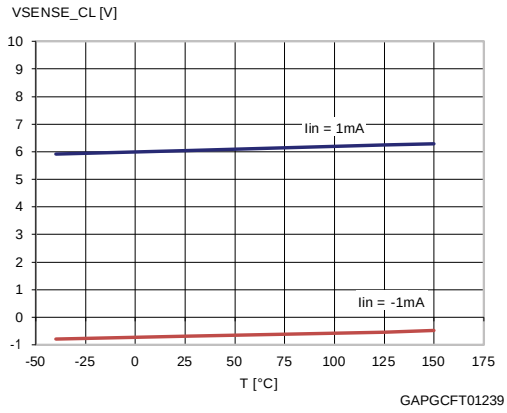


Figure 28: Vsenseh vs. Tcase

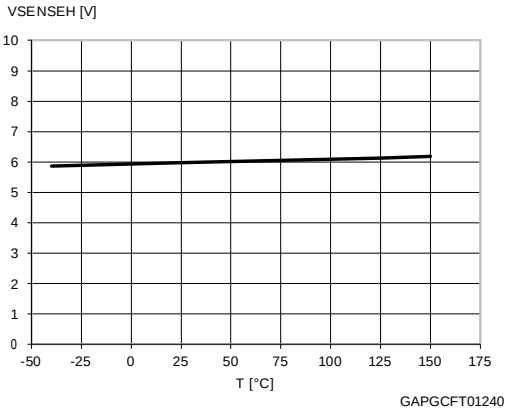
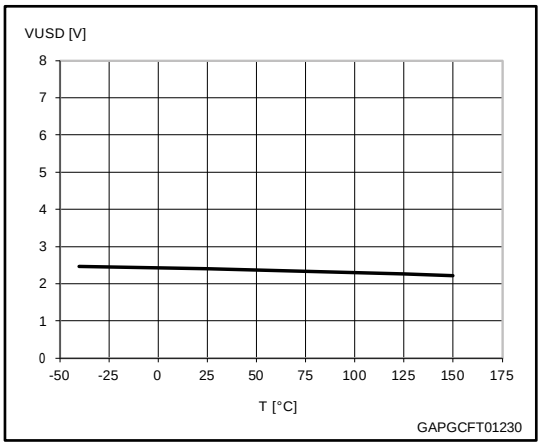


Figure 29: Undervoltage shutdown



3 Protections

3.1 Power limitation

The basic working principle of this protection consists of an indirect measurement of the junction temperature swing ΔT_j through the direct measurement of the spatial temperature gradient on the device surface in order to automatically shut off the output MOSFET as soon as ΔT_j exceeds the safety level of ΔT_{j_SD}. The protection prevents fast thermal transient effects and, consequently, reduces thermo-mechanical fatigue.

3.2 Thermal shutdown

If the junction temperature of the device exceeds the maximum allowed threshold (typically 175°C), it automatically switches off and the diagnostic indication is triggered. The device switches on again as soon as its junction temperature drops to T_R.

3.3 Current limitation

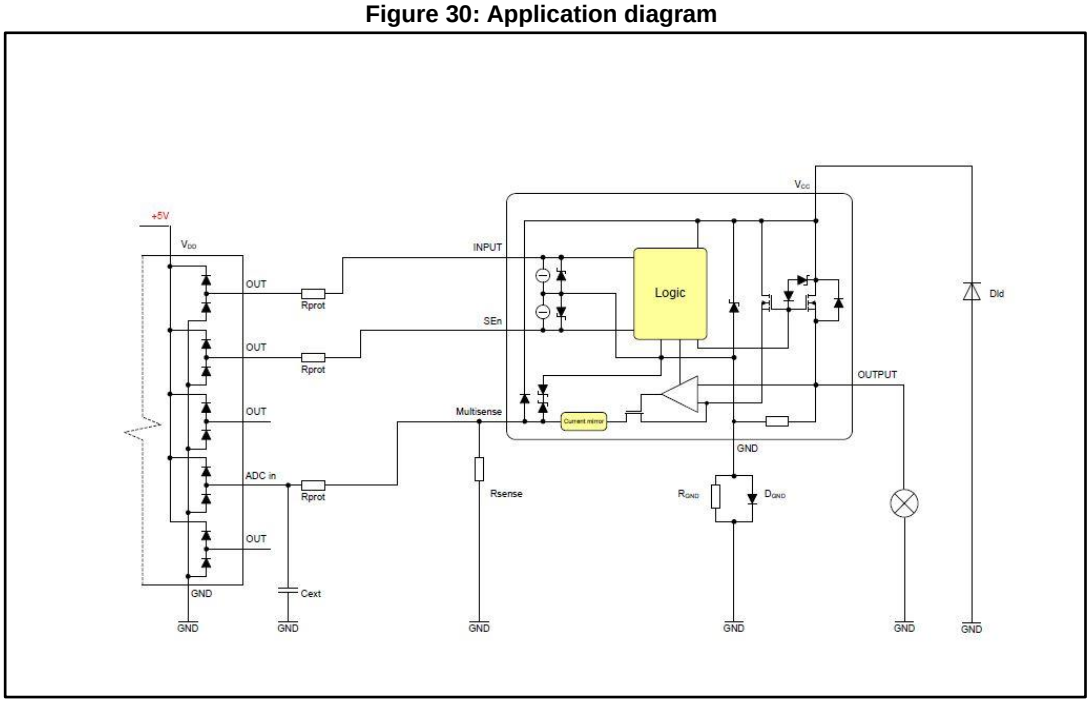
The device is equipped with an output current limiter in order to protect the silicon as well as the other components of the system (e.g. bonding wires, wiring harness, connectors, loads, etc.) from excessive current flow. Consequently, in case of short circuit, overload or during load power-up, the output current is clamped to a safety level, I_{LIMH}, by operating the output power MOSFET in the active region.

3.4 Negative voltage clamp

If the device drives inductive load, the output voltage reaches a negative value during turn off. A negative voltage clamp structure limits the maximum negative voltage to a certain value, V_{DEMAG}, allowing the inductor energy to be dissipated without damaging the device.

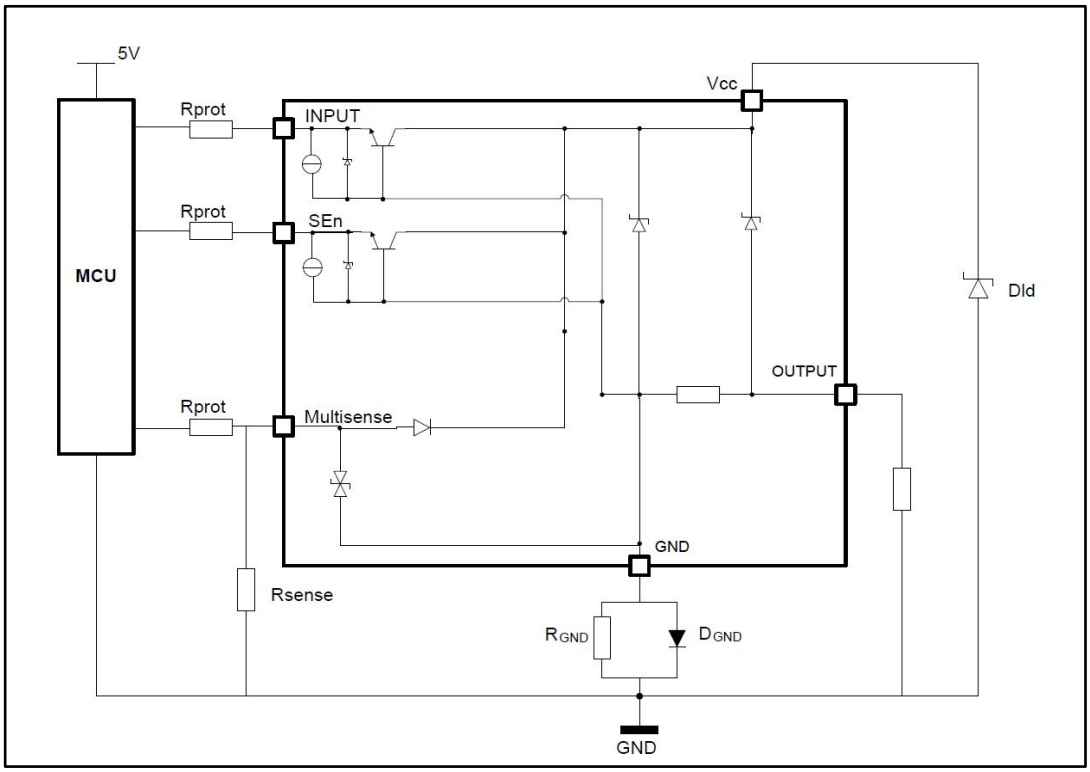
4 Application information

Figure 30: Application diagram



4.1 GND protection network against reverse battery

Figure 31: Simplified internal structure



4.1.1 Diode (DGND) in the ground line

A resistor (typ. R_{GND} = 4.7 kΩ) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift (≈600 mV) in the input threshold and in the status output values if the microprocessor ground is not common to the device ground. This shift does not vary if more than one HSD shares the same diode/resistor network.

4.2 Immunity against transient electrical disturbances

The immunity of the device against transient electrical emissions, conducted along the supply lines and injected into the V_{CC} pin, is tested in accordance with ISO7637-2:2011 (E) and ISO 16750-2:2010.

The related function performance status classification is shown in *Table 12: "ISO 7637-2 - electrical transient conduction along supply line"*.

Test pulses are applied directly to DUT (Device Under Test) both in ON and OFF-state and in accordance to ISO 7637-2:2011(E), chapter 4. The DUT is intended as the present device only, without components and accessed through V_{CC} and GND terminals.

Status II is defined in ISO 7637-1 Function Performance Status Classification (FPSC) as follows: “The function does not perform as designed during the test but returns automatically to normal operation after the test”.

Table 12: ISO 7637-2 - electrical transient conduction along supply line

Test Pulse 2011(E)	Test pulse severity level with Status II functional performance status		Minimum number of pulses or test time	Burst cycle / pulse repetition time		Pulse duration and pulse generator internal impedance
	Level	U_S (1)		min	max	
1	III	-112 V	500 pulses	0.5 s		2 ms, 10 Ω
2a (3)	III	+55 V	500 pulses	0.2 s	5 s	50 µs, 2 Ω
3a	IV	-220 V	1h	90 ms	100 ms	0.1 µs, 50 Ω
3b	IV	+150 V	1h	90 ms	100 ms	0.1 µs, 50 Ω
4 (2)	IV	-7 V	1 pulse			100 ms, 0.01 Ω
Load dump according to ISO 16750-2:2010						
Test B (3)(3)		40 V	5 pulse	1 min		400 ms, 2 Ω

Notes:

(1)U_S is the peak amplitude as defined for each test pulse in ISO 7637-2:2011(E), chapter 5.6.

(2)Test pulse from ISO 7637-2:2004(E).

(3)With 40 V external suppressor referred to ground (-40°C < T_j < 150 °C).

4.3 MCU I/Os protection

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line both to prevent the microcontroller I/O pins from latching-up and to protect the HSD inputs.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

Equation

$V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$

Calculation example:

For V_{CCpeak} = -150 V; $I_{latchup} \geq$ 20 mA; $V_{OH\mu C} \geq$ 4.5 V

7.5 kΩ ≤ R_{prot} ≤ 140 kΩ.

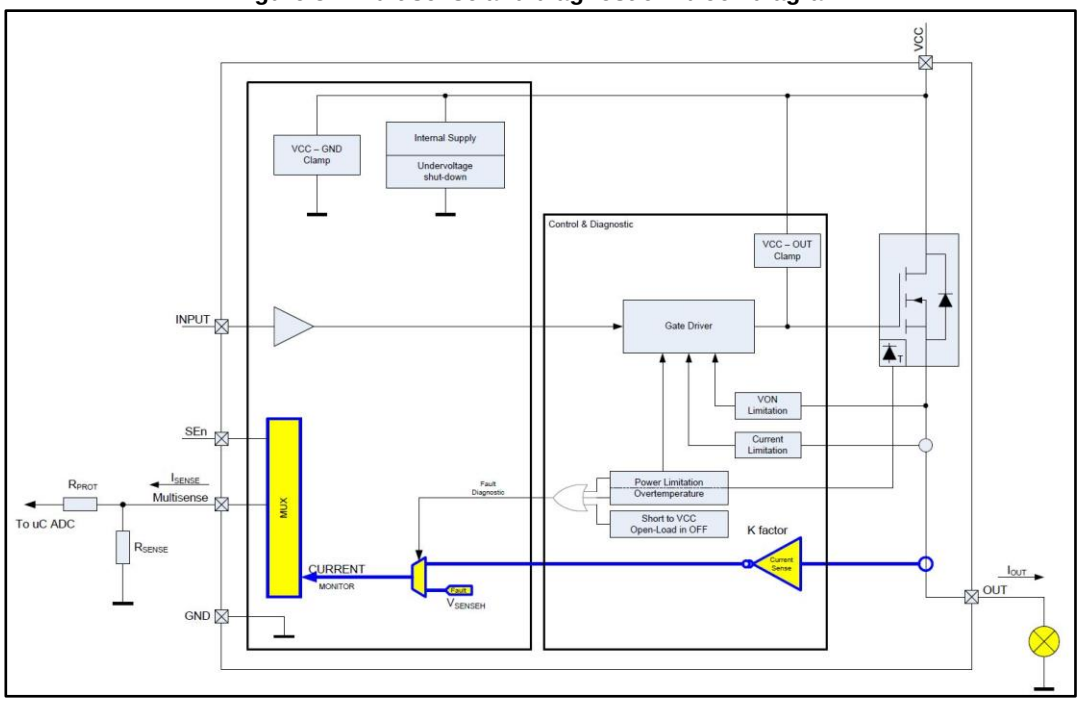
Recommended values: R_{prot} = 15 kΩ

4.4 Multisense - analog current sense

Diagnostic information on device and load status are provided by an analog output pin (Multisense) delivering the following signals:

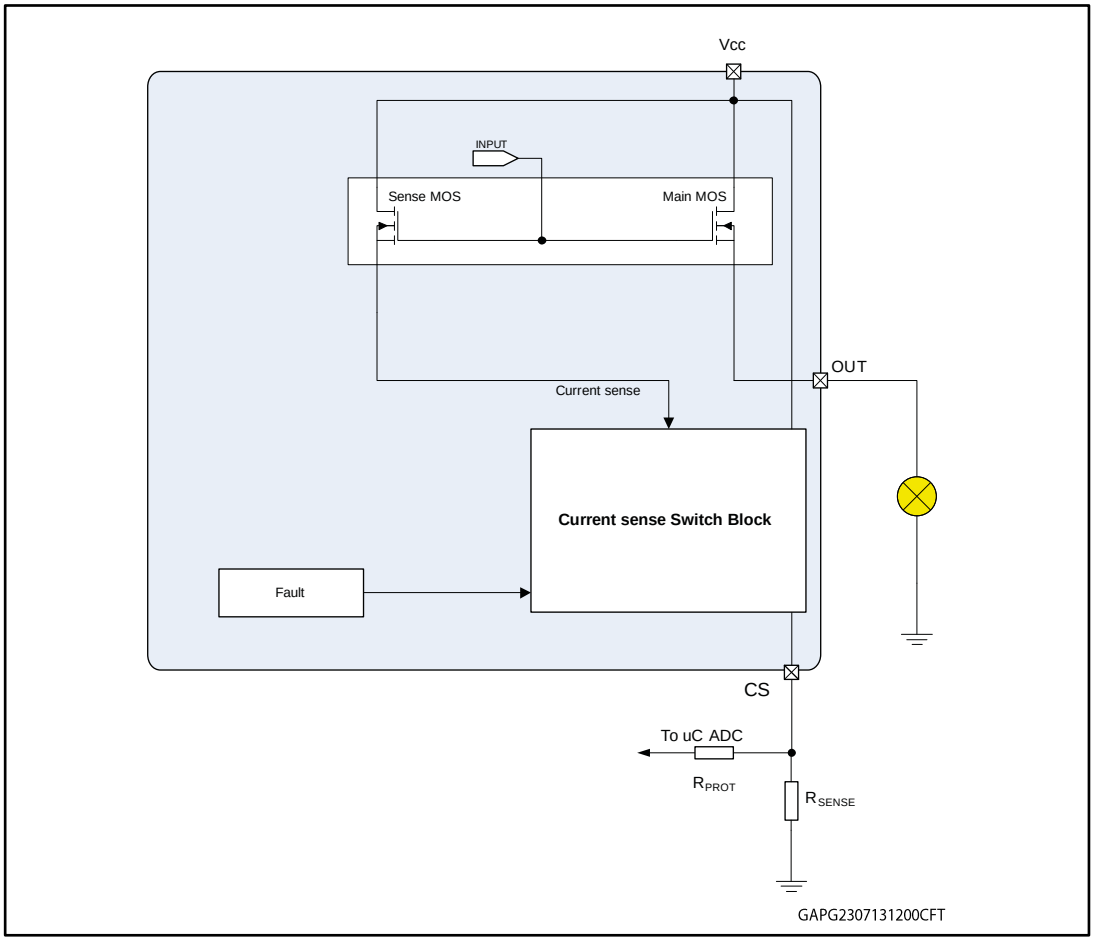
- Current monitor: current mirror of channel output current

Figure 32: Multisense and diagnostic – block diagram



4.4.1 Principle of Multisense signal generation

Figure 33: Multisense block diagram



Current sense

The Multisense output is capable of providing:

- Current mirror proportional to the load current in normal operation, delivering current proportional to the load according to known ratio named **K**
- Diagnostics flag in fault conditions delivering fixed voltage V_{SENSEH}

The current delivered by the current sense circuit, I_{SENSE}, can be easily converted to a voltage V_{SENSE} by using an external sense resistor, R_{SENSE}, allowing continuous load monitoring and abnormal condition detection.

Normal operation (channel ON, no fault, SEn active)

While device is operating in normal conditions (no fault intervention), V_{SENSE} calculation can be done using simple equations

Current provided by Multisense output: $I_{SENSE} = I_{OUT}/K$

Voltage on R_{SENSE}: $V_{SENSE} = R_{SENSE} \cdot I_{SENSE} = R_{SENSE} \cdot I_{OUT}/K$

Where:

- V_{SENSE} is voltage measurable on R_{SENSE} resistor
- I_{SENSE} is current provided from Multisense pin in current output mode
- I_{OUT} is current flowing through output
- K factor represents the ratio between PowerMOS cells and SenseMOS cells; its spread includes geometric factor spread, current sense amplifier offset and process parameters spread of the overall circuitry the specifying ratio between I_{OUT} and I_{SENSE}.

Failure flag indication

In case of power limitation/overtemperature, the fault is indicated by the Multisense pin which is switched to a “current limited” voltage source, V_{SENSEH}.

In any case, the current sourced by the Multisense in this condition is limited to I_{SENSEH}.

The typical behavior in case of overload or hard short circuit is shown in *Waveforms section*.

Figure 34: Analogue HSD – open-load detection in off-state

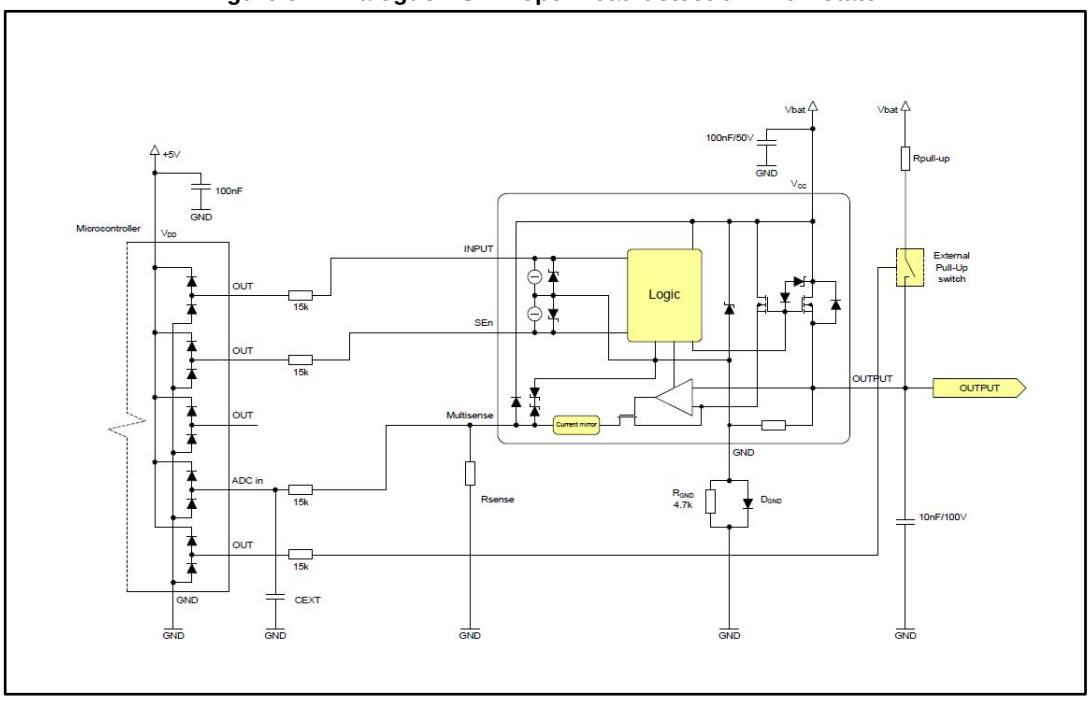


Figure 35: Open-load / short to VCC condition

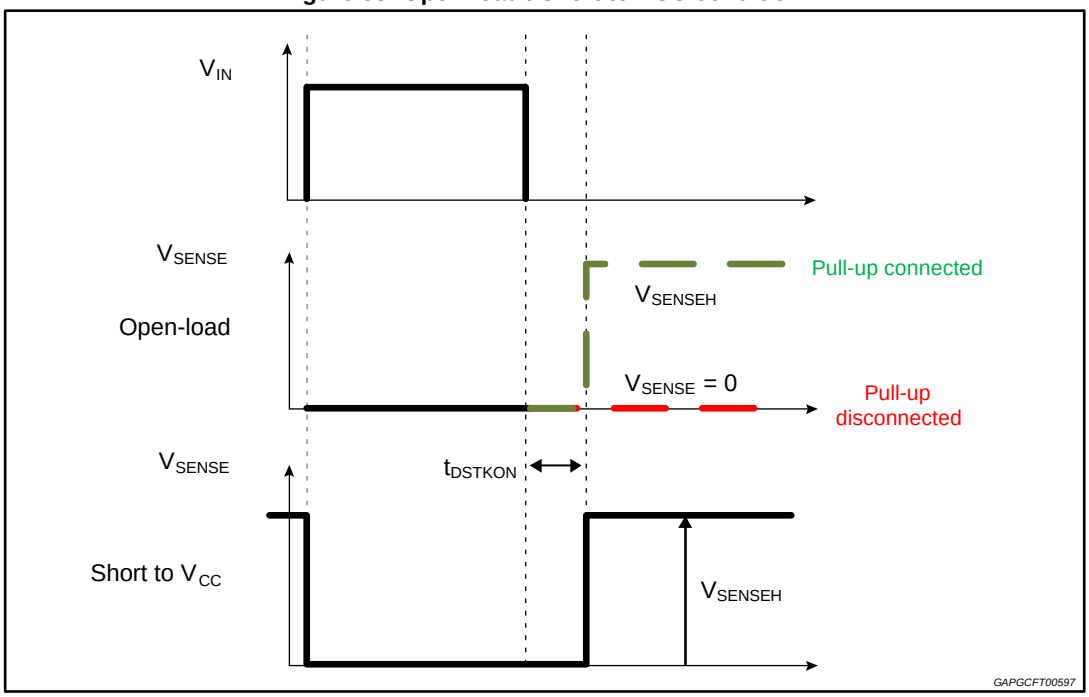


Table 13: Multisense pin levels in off-state

Condition	Output	Multisense	SEn
Open-load	$V_{OUT} > V_{OL}$	Hi-Z	L
		V_{SENSEH}	H
	$V_{OUT} < V_{OL}$	Hi-Z	L
		0	H
Short to V_{CC}	$V_{OUT} > V_{OL}$	Hi-Z	L
		V_{SENSEH}	H
Nominal	$V_{OUT} < V_{OL}$	Hi-Z	L
		0	H

4.4.2 Short to VCC and OFF-state open-load detection

Short to V_{CC}

A short circuit between V_{CC} and output is indicated by the relevant current sense pin set to V_{SENSEH} during the device off-state. Small or no current is delivered by the current sense during the on-state depending on the nature of the short circuit.

OFF-state open-load with external circuitry

Detection of an open-load in off mode requires an external pull-up resistor R_{PU} connecting the output to a positive supply voltage V_{PU}.

It is preferable that V_{PU} is switched off during the module standby mode in order to avoid the overall standby current consumption to increase in normal conditions, i.e. when load is connected.

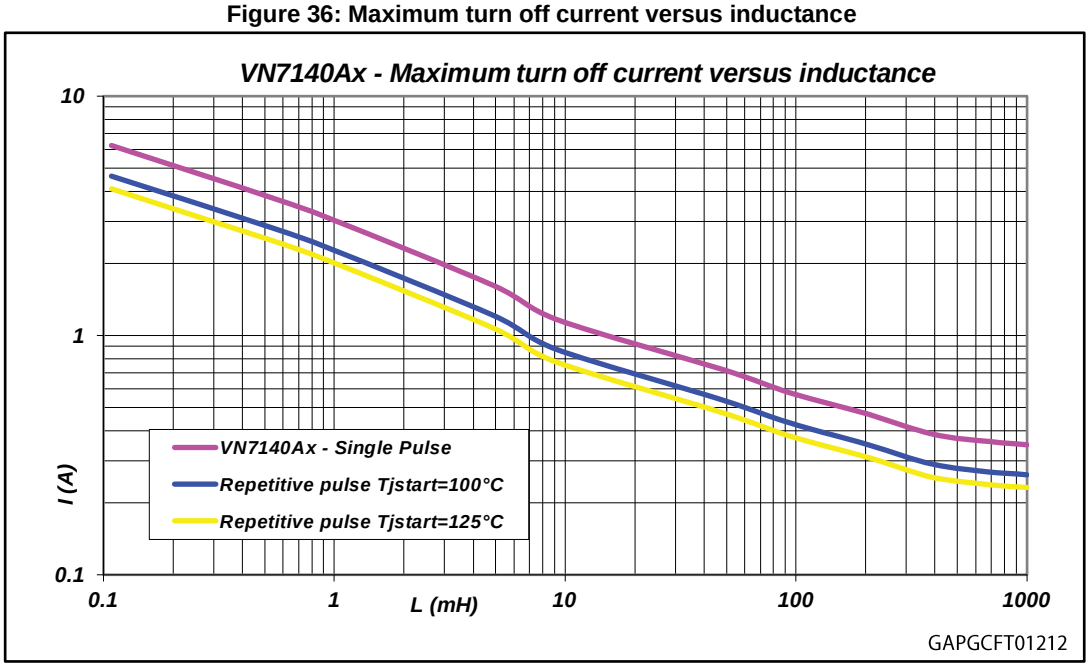
R_{PU} must be selected in order to ensure $V_{OUT} > V_{OLmax}$ in accordance with the following equation:

Equation

$$R_{PU} < \frac{V_{PU} - 4}{I_{L(off2)min\ @\ 4V}}$$

5 Maximum demagnetization energy (VCC = 16 V)

Figure 36: Maximum turn off current versus inductance



Values are generated with R_L = 0 Ω.

In case of repetitive pulses, T_{jstart} (at the beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

6 Package and PCB thermal data

6.1 SO-8 thermal data

Figure 37: S0-8 on two-layers PCB (2s0p to JEDEC JESD 51-5)

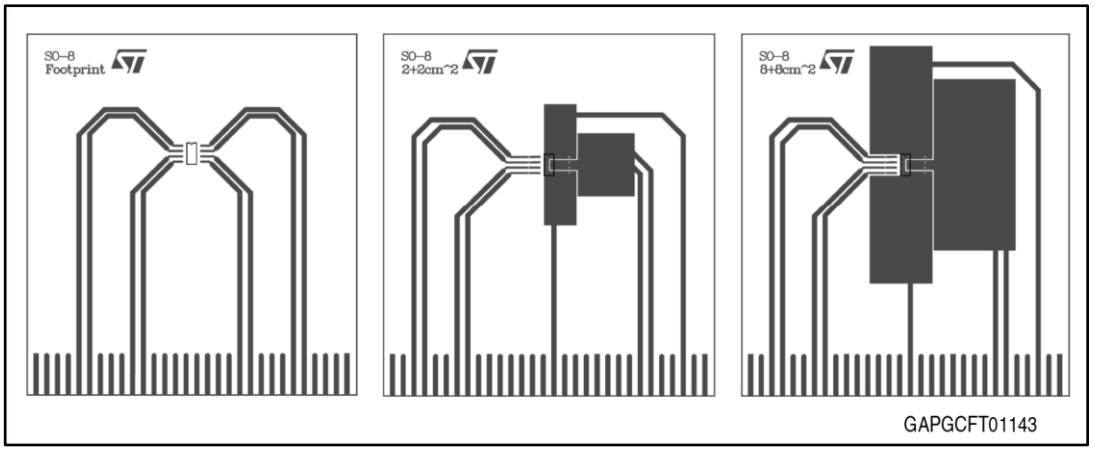


Figure 38: SO-8 on four-layers PCB (2s2p to JEDEC JESD 51-7)

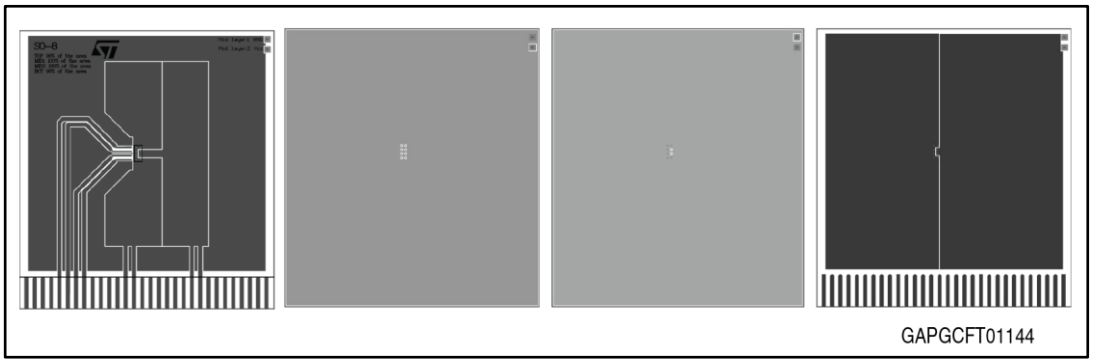


Table 14: PCB properties

Dimension	Value
Board finish thickness	1.6 mm +/- 10%
Board dimension	77 mm x 86 mm
Board Material	FR4
Copper thickness (top and bottom layers)	0.070 mm
Copper thickness (inner layers)	0.035 mm
Thermal vias separation	1.2 mm
Thermal via diameter	0.3 mm +/- 0.08 mm
Copper thickness on vias	0.025 mm
Heatsink copper area dimension (bottom layer)	Footprint, 2 + 2 cm^2 or 8 + 8 cm^2

Figure 39: SO-8 Rthj-amb vs PCB copper area in open box free air condition (one channel on)

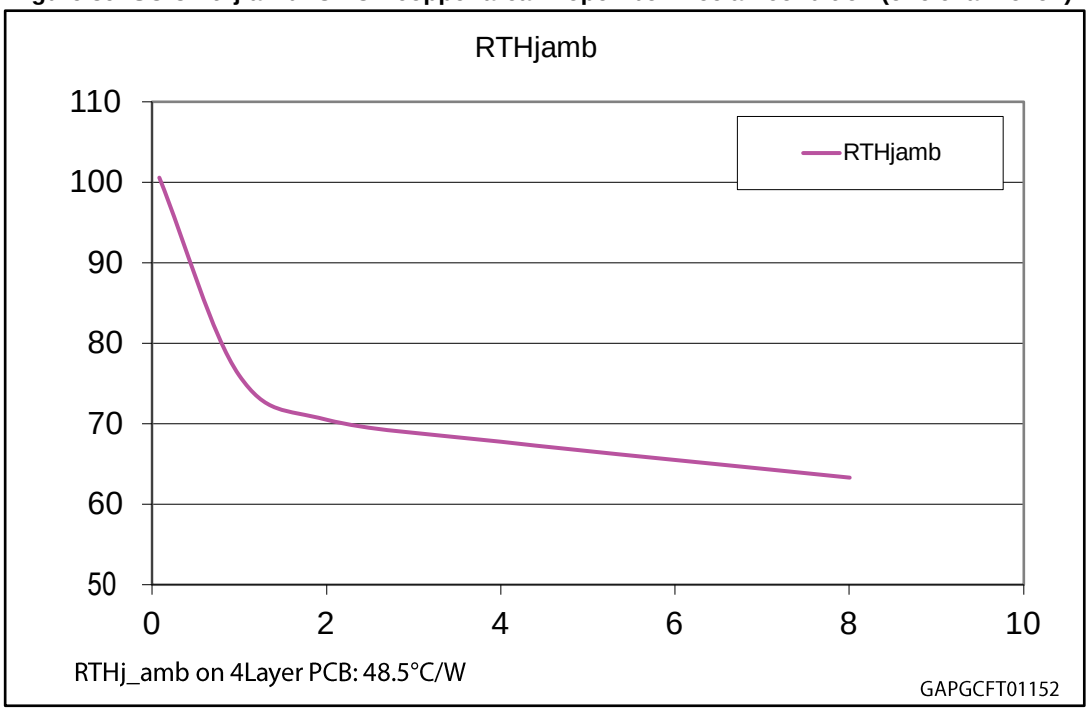
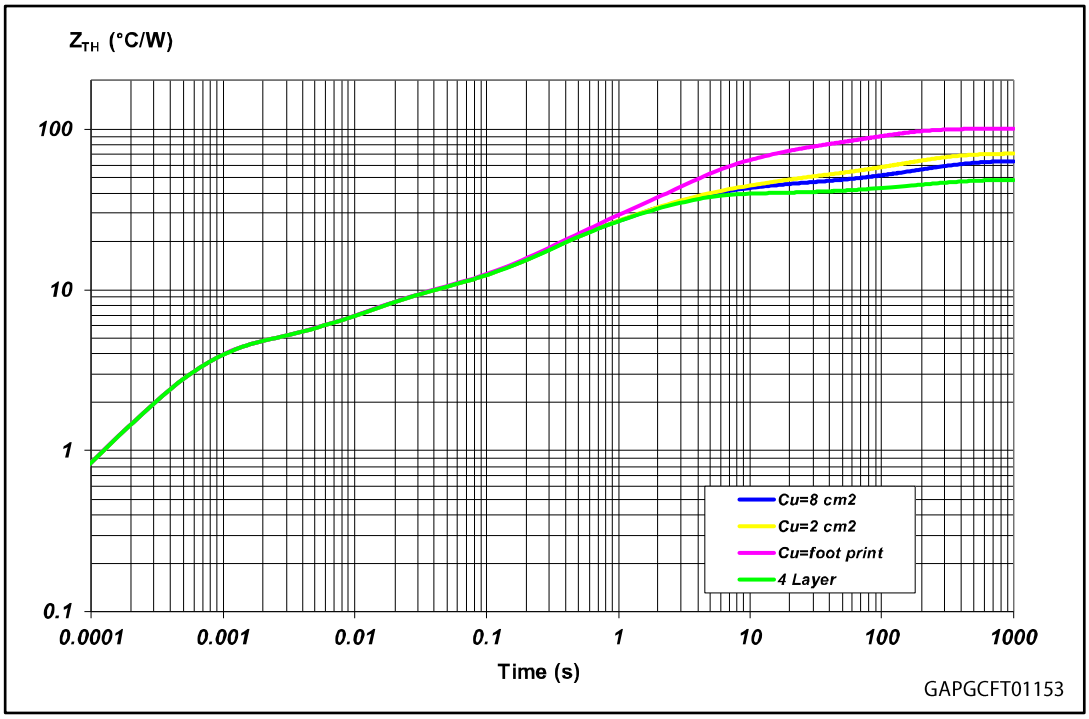


Figure 40: SO-8 thermal impedance junction ambient single pulse (one channel on)

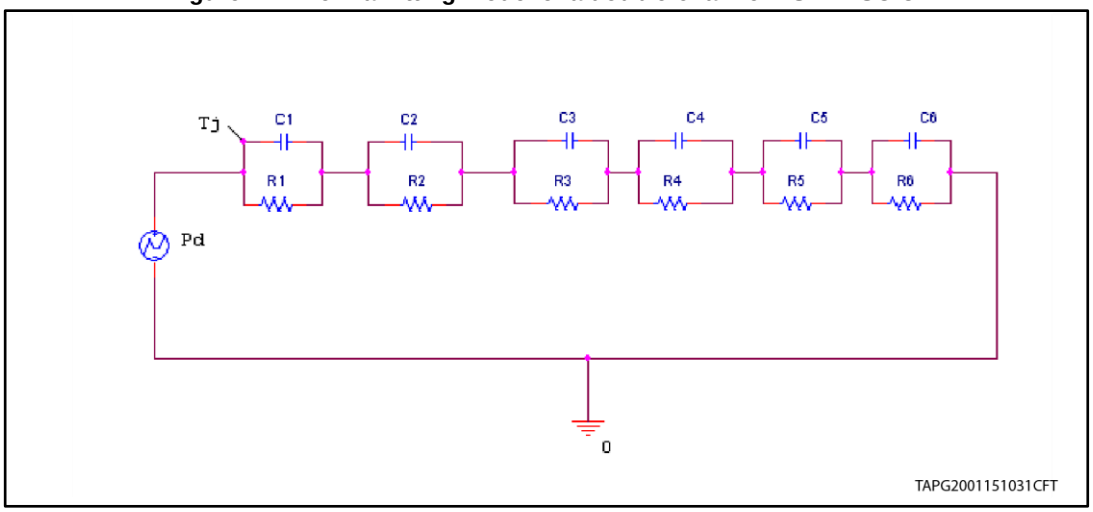


Equation: pulse calculation formula

$Z_{THδ} = R_{TH} \cdot δ + Z_{THtp} (1 - δ)$

where $δ = t_P/T$

Figure 41: Thermal fitting model of a double-channel HSD in SO-8



The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered.

Table 15: Thermal parameters

Area/island (cm^2)	Footprint	2	8	4L
R1 (°C/W)	4.2			
R2 (°C/W)	4.3			
R3 (°C/W)	10			
R4 (°C/W)	28	17	17	17
R5 (°C/W)	24	12	9	4
R6 (°C/W)	30	23	19	9
C1 (W.s/°C)	0.00012			
C2 (W.s/°C)	0.003			
C3 (W.s/°C)	0.03			
C4 (W.s/°C)	0.1			
C5 (W.s/°C)	0.4	0.8	0.8	0.8
C6 (W.s/°C)	3	7	11	22

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

7.1 SO-8 package information

Figure 42: SO-8 package outline

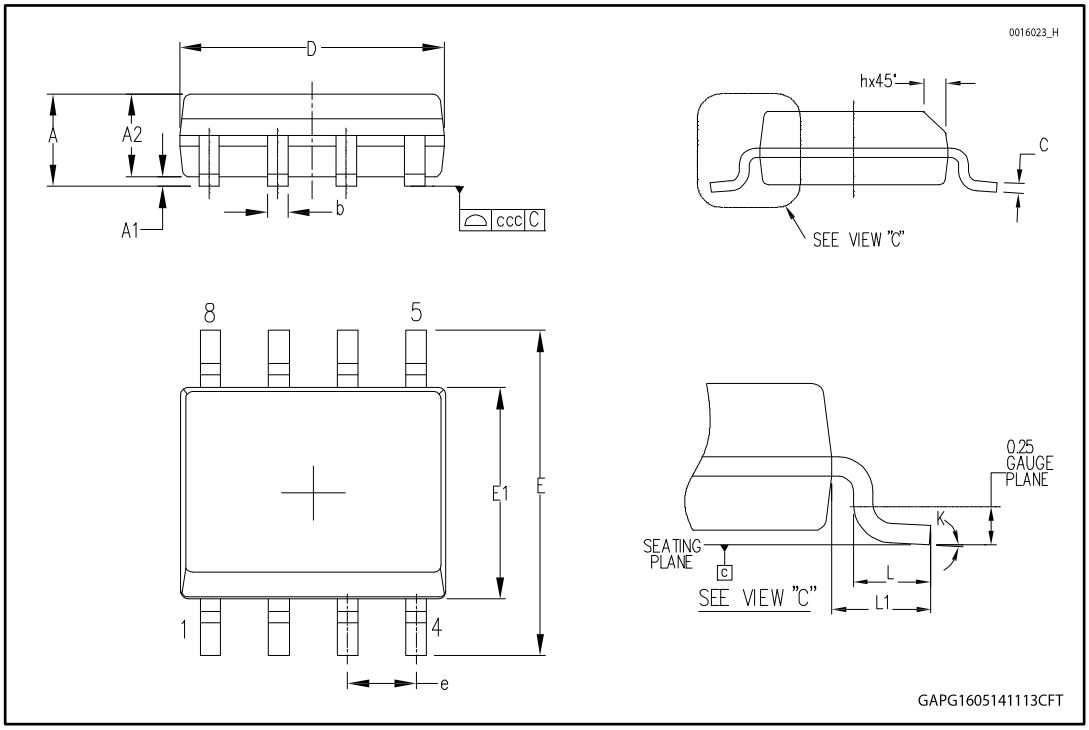


Table 16: SO-8 mechanical data

Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.28		0.48
c	0.17		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50

Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
L	0.40		1.27
L1		1.04	
k	0º		8º
ccc			0.10

7.2 SO-8 packing information

Figure 43: Reel for SO-8

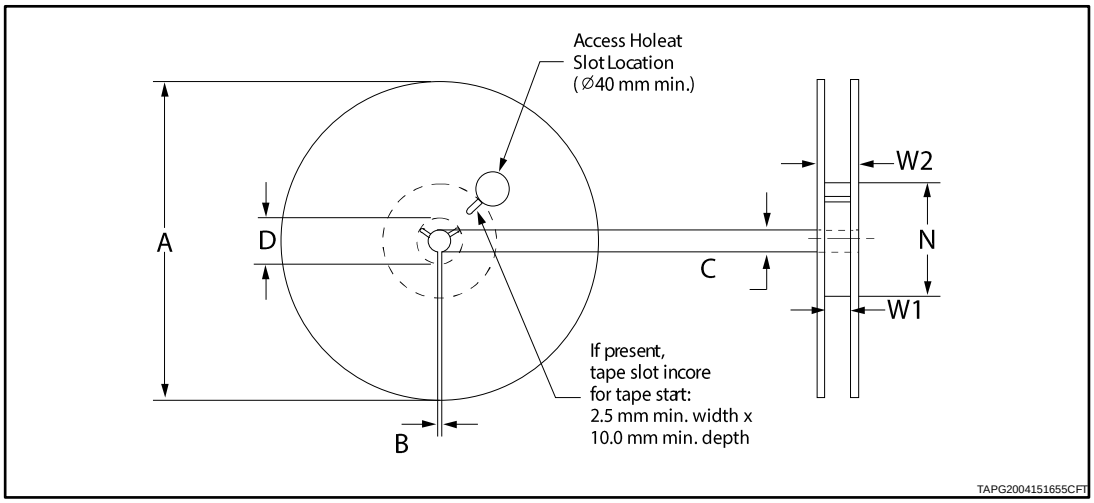


Table 17: Reel dimensions

Description	Value(1)
Base quantity	2500
Bulk quantity	2500
A (max)	330
B (min)	1.5
C (+0.5, -0.2)	13
D (min)	20.2
N	100
W1 (+2/ -0)	12.4
W2 (max)	18.4

Notes:

(1)All dimensions are in mm.

Figure 44: SO-8 carrier tape

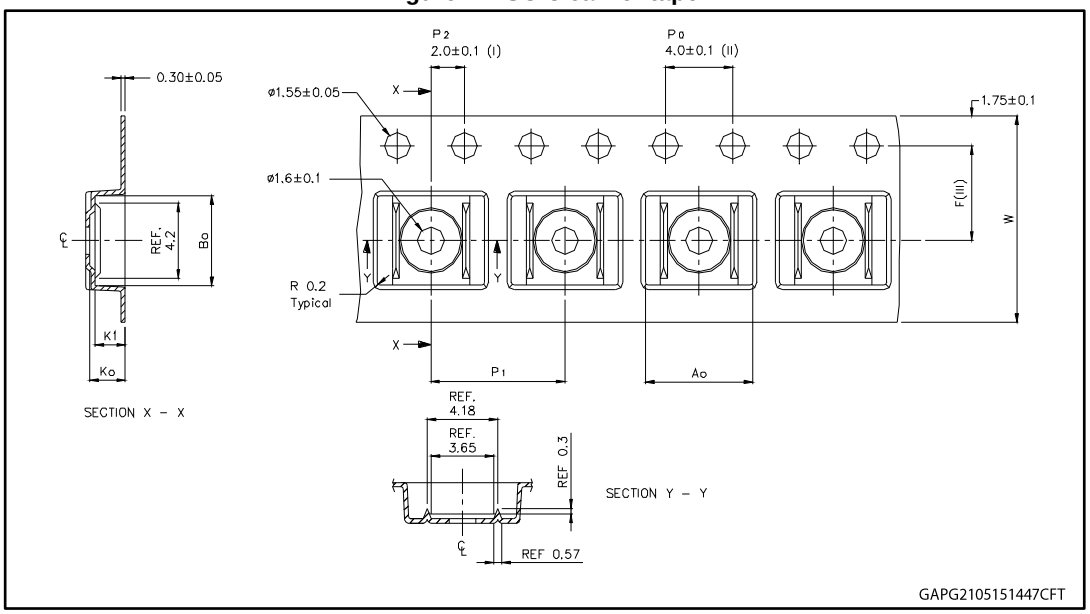


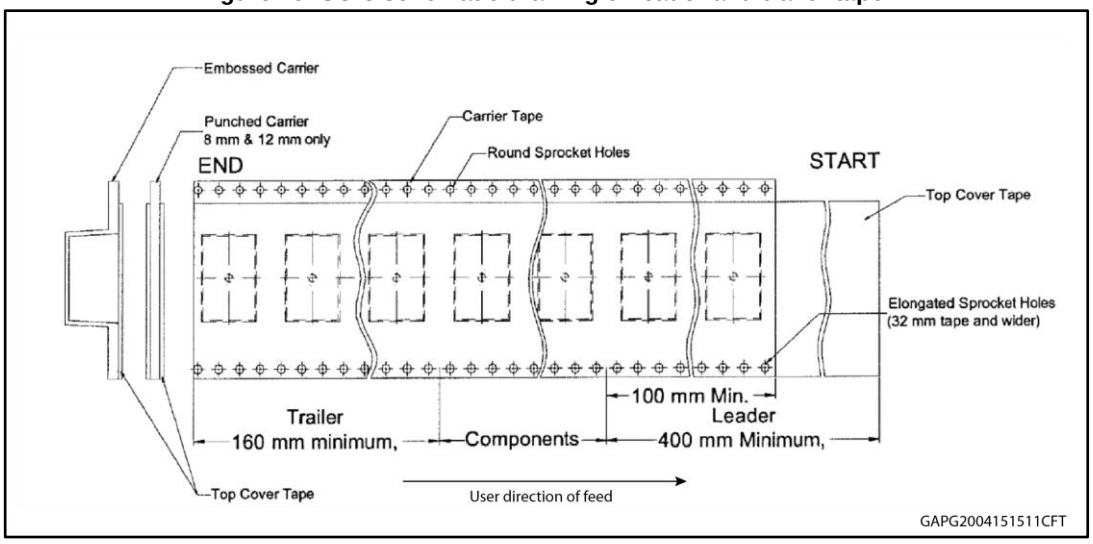
Table 18: SO-8 carrier tape dimensions

Description	Value[(1)]
A_0	6.50 ± 0.1
B_0	5.30 ± 0.1
K_0	2.20 ± 0.1
K_1	1.90 ± 0.1
F	5.50 ± 0.1
P_1	8.00 ± 0.1
W	12.00 ± 0.3

Notes:

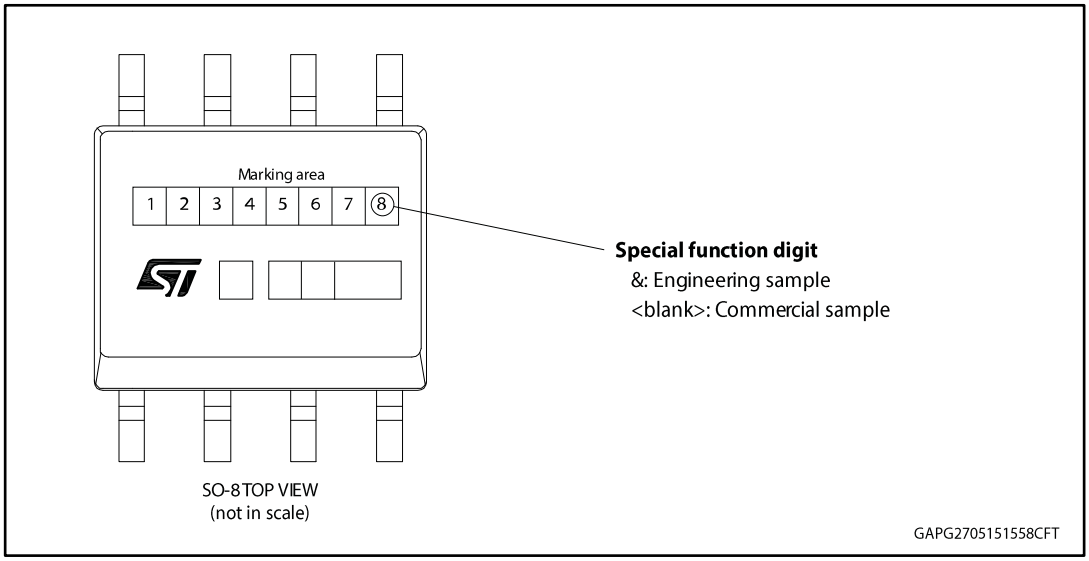
(1)All dimensions are in mm.

Figure 45: SO-8 schematic drawing of leader and trailer tape



7.3 SO-8 marking information

Figure 46: SO-8 marking information



Engineering Samples: these samples can be clearly identified by a dedicated special symbol in the marking of each unit. These samples are intended to be used for electrical compatibility evaluation only; usage for any other purpose may be agreed only upon written authorization by ST. ST is not liable for any customer usage in production and/or in reliability qualification trials.

Commercial Samples: fully qualified parts from ST standard production with no usage restrictions

8 Order code

Table 19: Device summary

Package	Order code
	Tape and reel
SO-8	VN7140AS12TR

9 Revision history

Table 20: Document revision history

Date	Revision	Changes
05-Oct-2016	1	Initial release.
07-Feb-2018	2	Document status promoted from target specification to production data.

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